NCE N-Channel Enhancement Mode Power MOSFET

Description

The NCE6020AL uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications.

General Features

V_{DS} =60V,I_D =20A

 $R_{DS(ON)}$ <25m Ω @ V_{GS} =10V

 $R_{DS(ON)}$ <31m Ω @ V_{GS} =4.5V

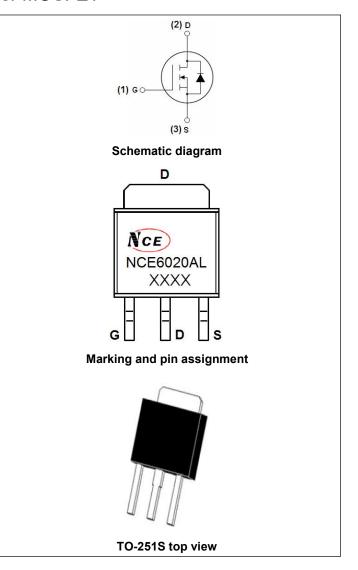
- High density cell design for ultra low Rdson
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high E_{AS}
- Excellent package for good heat dissipation
- Special process technology for high ESD capability

Application

- Power switching application
- Hard switched and high frequency circuits
- Uninterruptible power supply

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100% AVds TESTED!



Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCE6020AL	NCE6020AL	TO-251S	-	-	-

Absolute Maximum Ratings (T_C=25℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	60	V
Gate-Source Voltage	V _G s	±20	V
Drain Current-Continuous	I _D	20	Α
Drain Current-Continuous(T _C =100 °C)	I _D (100°C)	14	А
Pulsed Drain Current	I _{DM}	60	Α
Maximum Power Dissipation	P _D	45	W
Derating factor		0.3	W/℃
Single pulse avalanche energy (Note 5)	Eas	72	mJ
Operating Junction and Storage Temperature Range	T_{J}, T_{STG}	-55 To 175	$^{\circ}$



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NCE6020AL

Thermal Characteristic

Thermal Resistance,Junction-to-Case ^(Note 2) ReJC 3.3 °C/W

Electrical Characteristics (Tc=25 ℃ unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit	
Off Characteristics			•				
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250µA	60	-	-	V	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =60V,V _{GS} =0V	-	-	1	μA	
Gate-Body Leakage Current	Igss	V _{GS} =±20V,V _{DS} =0V	-	-	±100	nA	
On Characteristics (Note 3)			•				
Gate Threshold Voltage	Threshold Voltage V _{GS(th)} V _{DS} =V _{GS} ,I _D =250µA		1.2	1.6	2.5	V	
	_	V _{GS} =10V, I _D =20A	-	21	25	0	
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =4.5V, I _D =20A		25.5	31	mΩ	
Forward Transconductance	G FS	V _{DS} =5V,I _D =5A	11	-	-	S	
Dynamic Characteristics (Note4)							
Input Capacitance	C _{lss}	\/ 00\/\\ 0\/	-	973.2	-	PF	
Output Capacitance	Coss	V _{DS} =30V,V _{GS} =0V, F=1.0MHz	-	61.2	-	PF	
Reverse Transfer Capacitance	C _{rss}	F=1.UMHZ	-	58.8	-	PF	
Switching Characteristics (Note 4)							
Turn-on Delay Time	t _{d(on)}		-	5	-	nS	
Turn-on Rise Time	t _r	V _{DD} =30V,I _D =2A,R _L =6.7Ω	-	2.6	-	nS	
Turn-Off Delay Time	t _{d(off)}	V_{GS} =10V, R_{G} =3 Ω	-	16.1	-	nS	
Turn-Off Fall Time	t _f		-	2.3	-	nS	
Total Gate Charge	Qg	V/ 00V/1 4.5A	-	25		nC	
Gate-Source Charge	Qgs	V _{DS} =30V,I _D =4.5A,	-	4.5		nC	
Gate-Drain Charge	Q _{gd}	V _{GS} =10V	-	6.5		nC	
Drain-Source Diode Characteristics			•				
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =20A	-		1.2	V	
Diode Forward Current (Note 2)	Is		-	-	20	Α	
Reverse Recovery Time	t _{rr}	TJ = 25°C, IF =20A	-	29	-	nS	
Reverse Recovery Charge	Qrr	di/dt = 100A/µs ^(Note3)	-	49	-	nC	
Forward Turn-On Time	t _{on}	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD					

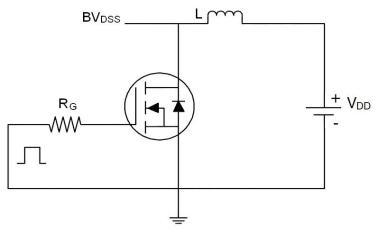
Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- **2.** Surface Mounted on FR4 Board, $t \le 10$ sec.
- 3. Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
- 4. Guaranteed by design, not subject to production
- **5.** EAS condition:Tj=25 $^{\circ}$ C,VDD=30V,VG=10V,L=0.5mH,Rg=25 Ω

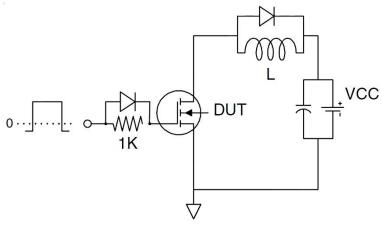


Test Circuit

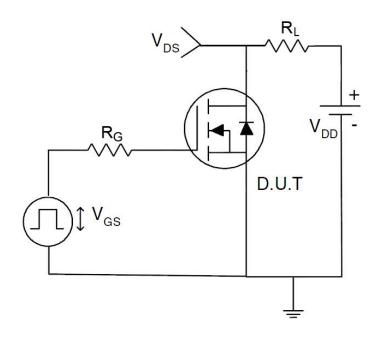
1) E_{AS} test Circuit



2) Gate charge test Circuit



3) Switch Time Test Circuit





Typical Electrical and Thermal Characteristics (Curves)

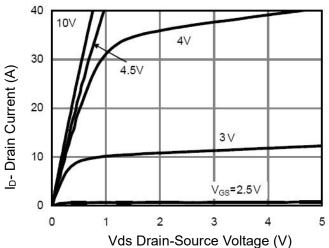


Figure 1 Output Characteristics

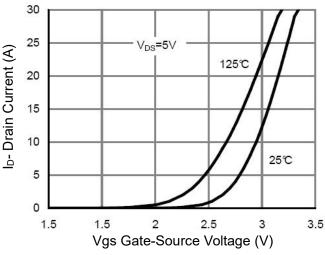
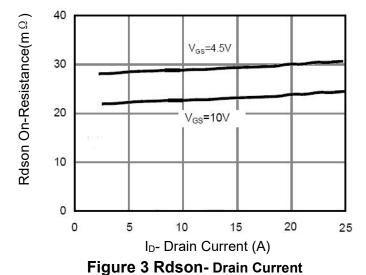


Figure 2 Transfer Characteristics



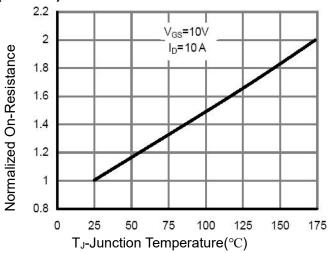


Figure 4 Rdson-Junction Temperature

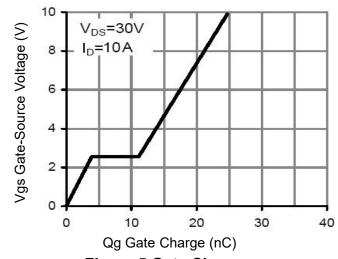


Figure 5 Gate Charge

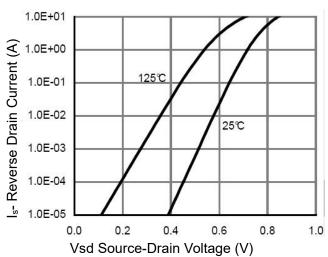


Figure 6 Source- Drain Diode Forward



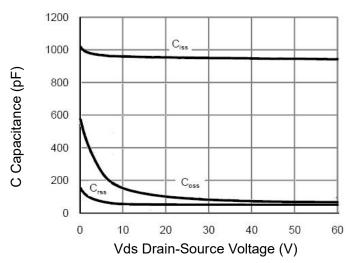


Figure 7 Capacitance vs Vds

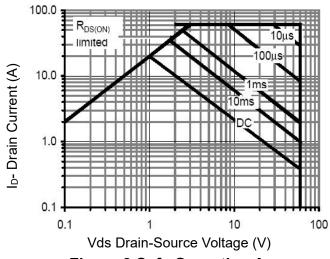


Figure 8 Safe Operation Area

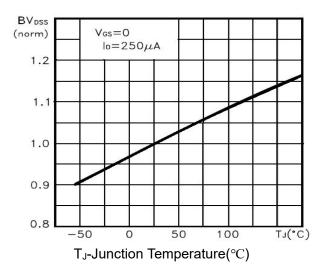


Figure 9 BV_{DSS} vs Junction Temperature

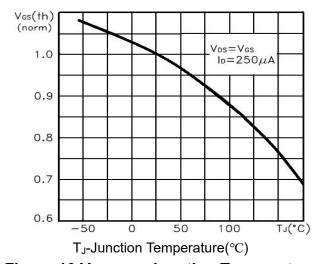


Figure 10 V_{GS(th)} vs Junction Temperature

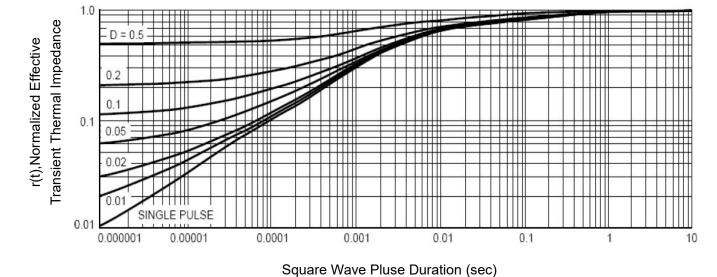
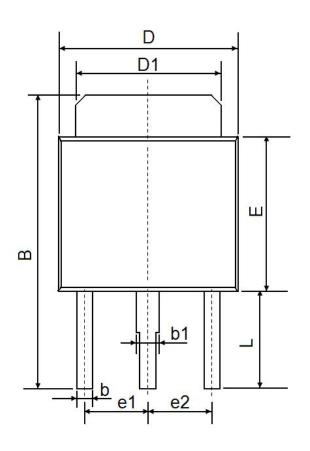
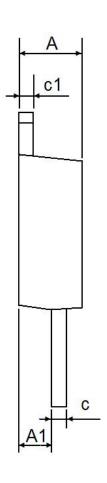


Figure 11 Normalized Maximum Transient Thermal Impedance



TO-251S Package Information





Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
Α	2.250	2.350	0.089	0.093
A1	1.150	1.250	0.045	0.049
В	10.200	10.800	0.402	0.425
b	0.550	0.650	0.022	0.026
b1	0.750	0.850	0.030	0.033
С	0.480	0.540	0.019	0.021
c1	0.480	0.540	0.019	0.021
D	6.400	6.600	0.252	0.260
D1	5.250	5.350	0.207	0.211
E	5.400	5.600	0.213	0.220
e1	2.300 TYP		0.091 TYP	
e2	2.300 TYP		0.091 TYP	
L	3.300	3.700	0.130	0.146



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